

DERWENT-ACC-NO: 2002-253019

DERWENT-WEEK: 200230

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TITLE: Contact etching method of integrated circuit which can
reduce the contact resistance and increase the stability
effectively

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PRIORITY-DATA: 1998TW-0110328 (June 26, 1998)

PATENT-FAMILY:

| PUB-NO | PUB-DATE | LANGUAGE | PAGES | MAIN-IPC |
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| TW 442916 A | June 23, 2001 | N/A | 000 | H01L 021/768 |

APPLICATION-DATA:

| PUB-NO | APPL-DESCRIPTOR | APPL-NO | APPL-DATE |
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| TW 442916A | N/A | 1998TW-0110328 | June 26, 1998 |

INT-CL (IPC): H01L021/768

ABSTRACTED-PUB-NO: TW 442916A

BASIC-ABSTRACT:

NOVELTY - The present invention discloses a contact etching method of integrated circuit to process with CH₄/O₂ plasma simultaneously during stripping the photoresist, which can reduce the contact resistance and increase the stability effectively. The method comprises: first, providing a

semiconductor substrate covered with a dielectric layer and a photoresist layer having contact hole pattern; then, proceeding the main etching to the dielectric layer without being covered by the photoresist layer for forming the contact hole; then, proceeding the first photoresist strip, and proceeding the in-situ soft etching for forming the contact hole; finally, proceeding the second photoresist strip to clean up the photoresist thoroughly.

CHOSEN-DRAWING: Dwg.1/1

TITLE-TERMS: CONTACT ETCH METHOD INTEGRATE CIRCUIT CAN REDUCE
CONTACT
RESISTANCE INCREASE STABILISED EFFECT

DERWENT-CLASS: L03 U11

CPI-CODES: L04-C06B; L04-C07D;

EPI-CODES: U11-C05D;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C2002-075699

Non-CPI Secondary Accession Numbers: N2002-195132